

CA3080A

2MHz, Operational Transconductance Amplifier (OTA)

The CA3080 and CA3080A types are GatabLe-Gain Blocks which utilize the unique operational transconductance amplifier (OTA) concept described in Application Note AN6668, "Applications of the CA3080 and CA3080A High-Performance Operational Transconductance Amplifiers".

The CA3080 and CA3080A types have differential input and a single-ended, push-pull, class A output. In addition, these types have an amplifier bias input which may be used either for gating or for linear gain control. These types also have a high output impedance and their transconductance (g_M) is directly proportional to the amplifier bias current (I_{ABC}).

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All re-creations are done with the approval of the Original Component Manufacturer (OCM).

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
 - Class Q Military
 - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
 - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OCM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

FOR REFERENCE ONLY



CA3080, CA3080A

2MHz, Operational Transconductance Amplifier (OTA)

November 1996

Features

•	Slew Rate (Unity Gain, Compensated) 50V/µs
•	Adjustable Power Consumption
•	Flexible Supply Voltage Range $\ldots \ldots \pm 2V$ to $\pm 15V$
•	Fully Adjustable Gain0 to $g_M R_L$ Limit
•	Tight g _M Spread:
	- CA3080 2:1
	- CA3080A1.6:1
•	Extended g _M Linearity3 Decades

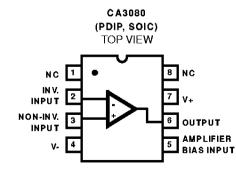
Applications

- Sample and Hold
 Multiplier
- Multiplexer
- Comparator
- Voltage Follower
- Comparator

Ordering Information

PART NUMBER (BRAND)	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CA3080	0 to 70	8 Pin Metal Can	T8.C
CA3080A	-55 to 125	8 Pin Metal Can	T8.C
CA3080AE	-55 to 125	8 Ld PDIP	E8.3
CA3080AM (3080A)	-55 to 125	8 Ld SOIC	M8.15
CA3080AM96 (3080A)	-55 to 125	8 Ld SOIC Tape and Reel	M8.15
CA3080E	0 to 70	8 Ld PDIP	E8.3
CA3080M (3080)	0 to 70	8 Ld SOIC	M8.15
CA3080M96 (3080)	0 to 70	8 Ld SOIC Tape and Reel	M8.15

Pinouts



NOTE: Pin 4 is connected to case.

Description

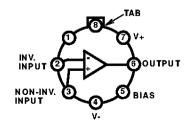
The CA3080 and CA3080A types are Gatable-Gain Blocks which utilize the unique operational-transconductanceamplifier (OTA) concept described in Application Note AN6668, "Applications of the CA3080 and CA3080A High-Performance Operational Transconductance Amplifiers".

The CA3080 and CA3080A types have differential input and a single-ended, push-pull, class A output. In addition, these types have an amplifier bias input which may be used either for gating or for linear gain control. These types also have a high output impedance and their transconductance (g_M) is directly proportional to the amplifier bias current (I_{ABC}).

The CA3080 and CA3080A types are notable for their excellent slew rate ($50V/\mu s$), which makes them especially useful for multiplexer and fast unity-gain voltage followers. These types are especially applicable for multiplexer applications because power is consumed only when the devices are in the "ON" channel state.

The CA3080A's characteristics are specifically controlled for applications such as sample-hold, gain-control, multiplexing, etc.

CA3080 (Metal Can) Top View



Absolute Maximum Ratings

Supply Voltage (Between V+ and V- Terminal)
Differential Input Voltage
Input Voltage
Input Signal Current 1mA
Amplifier Bias Current (I _{ABC})
Output Short Circuit Duration (Note 1) No Limitation

Operating Conditions

Temperature Range

iompolatato i tango	
CA3080	0°C to 70°C
CA3080A	5°C to 125°C

Thermal Information

Thermal Resistance (Typical, Note 2)	θ _{JA} (^o C/W)	θ _{JC} (^o C/W)
PDIP Package	130	N/A
SOIC Package	170	N/A
Metal Can Package	200	120
Maximum Junction Temperature (Metal Car	1)	175 ⁰ C
Maximum Junction Temperature (Plastic F	ackage)	150 ⁰ C
Maximum Storage Temperature Range	65	5°C to 150°C
Maximum Lead Temperature (Soldering 1	0s)	300 ⁰ C
(SOIC - Lead Tips Only)		

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

1. Short circuit may be applied to ground or to either supply.

2. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

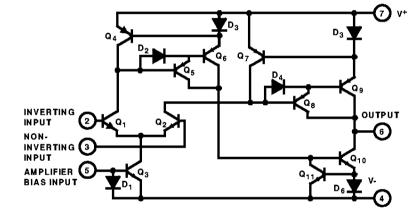
nent Design, V _{SUPPLY} = ±15V, Unless Otherwise Specified
ЯП

PARAMETER				CA3080			CA3080A			
		TEST CONDITIONS	TEMP	MIN	ΤΥΡ	MAX	MIN	ΤΥΡ	MAX	UNITS
Input Offset Voltage		$I_{ABC} = 5\mu A$	25	-	0.3	-	-	0.3	2	mV
		I _{ABC} = 500μA	25	-	0.4	5	-	0.4	2	mV
			Full	-	-	6	-	-	5	mV
Input Offset Voltage Cha	ange	I _{ABC} = 500μA to 5μA	25	-	0.2	-	-	0.1	3	mV
Input Offset Voltage Ten	np. Drift	I _{ABC} = 100μA	Full	-	-	-	-	3.0	-	μV/ ^o C
Input Offset Voltage	Positive	I _{ABC} = 500μA	25	-	-	150	-	-	150	μV/V
Sensitivity	Negative		25	-	-	150	-	-	150	μV/V
Input Offset Current		$I_{ABC} = 500 \mu A$	25	-	0.12	0.6	-	0.12	0.6	μA
Input Bias Current		$I_{ABC} = 500 \mu A$	25	-	2	5	-	2	5	μA
			Full	-	-	7	-	-	1 5	μA
Differential Input Current		$I_{ABC} = 0, V_{DIFF} = 4V$	25	-	0.008	-	-	0.008	5	nA
Amplifier Bias Voltage		$I_{ABC} = 500 \mu A$	25	-	0.71	-	-	0.71	-	V
Input Resistance		$I_{ABC} = 500 \mu A$	25	10	26	-	10	26	-	kΩ
Input Capacitance		$I_{ABC} = 500 \mu A$, f = 1MHz	25	-	3.6	-	-	3.6	-	pF
Input-to-Output Capacitance		$I_{ABC} = 500 \mu A$, f = 1MHz	25	-	0.024	-	-	0.024	-	рF
Common-Mode Input-Voltage Range		I _{ABC} = 500μA	25	12 to -12	13.6 to -14.6	-	12 to -12	13.6 to -14.6	-	V
Forward Transconductance (Large Signal)		$I_{ABC} = 500 \mu A$	25	6700	9600	13000	7700	9600	12000	μS
			Full	5400	-	-	4000	-	-	μS
Output Capacitance		I _{ABC} = 500μA, f = 1MHz	25	-	5.6	-	-	5.6	-	pF
Output Resistance		I _{ABC} = 500μA	25	-	15	-	-	15	-	MΩ
Peak Output Current		$I_{ABC} = 5\mu A, R_L = 0\Omega$	25	-	5	-	3	5	7	μΑ
		$I_{ABC} = 500 \mu A, R_L = 0 \Omega$	25	350	500	650	350	500	650	μA
			Full	300	-	-	300	-	-	μA

			ITIONS TEMP	CA3080			CA3080A			
PARAMET	ER	TEST CONDITIONS		MIN	ΤΥΡ	MAX	MIN	ΤΥΡ	MAX	UNITS
Peak Output	Positive	$I_{ABC} = 5\mu A, R_L = \infty$	25	-	13.8	-	12	13.8	-	V
Voltage	Negative		25	-	-14.5	-	-12	-14.5	-	V
	Positive	I _{ABC} = 500µA, R _L = ∞	25	12	13.5	-	12	13.5	-	V
	Negative		25	-12	-14.4	-	-12	-14.4	-	V
Amplifier Supply Current		$I_{ABC} = 500 \mu A$	25	0.8	1	1.2	0.8	1	1.2	mA
Device Dissipation		$I_{ABC} = 500 \mu A$	25	24	30	36	24	30	36	mW
Magnitude of Leakage Current		$I_{ABC} = 0, V_{TP} = 0$	25	-	0.08	-	-	0.08	5	nA
		$I_{ABC} = 0, V_{TP} = 36V$	25	-	0.3	-	-	0.3	5	nA
Propagation Delay		I _{ABC} = 500μA	25	-	45	-	-	45	-	ns
Common-Mode Rejection Ratio		I _{ABC} = 500μA	25	80	11 0	-	80	11 0	-	dB
Open-Loop Bandwidth		I _{ABC} = 500μA	25	-	2	-	-	2	-	MHz
Slew Rate		Uncompensated	25	-	75	-	-	75	-	V/µs
		Compensated	25	-	50	-	-	50	-	V/µs

Electrical Specifications For Equipment Design, V_{SUPPLY} = ±15V, Unless Otherwise Specified (Continued)

Schematic Diagram



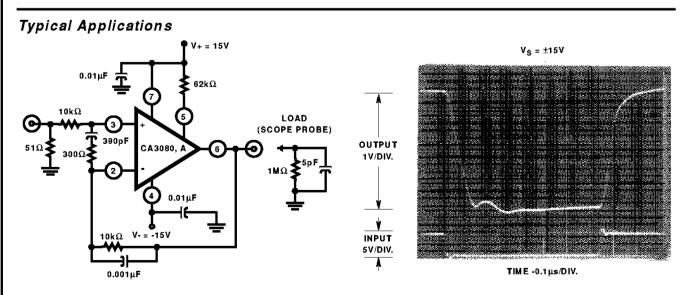
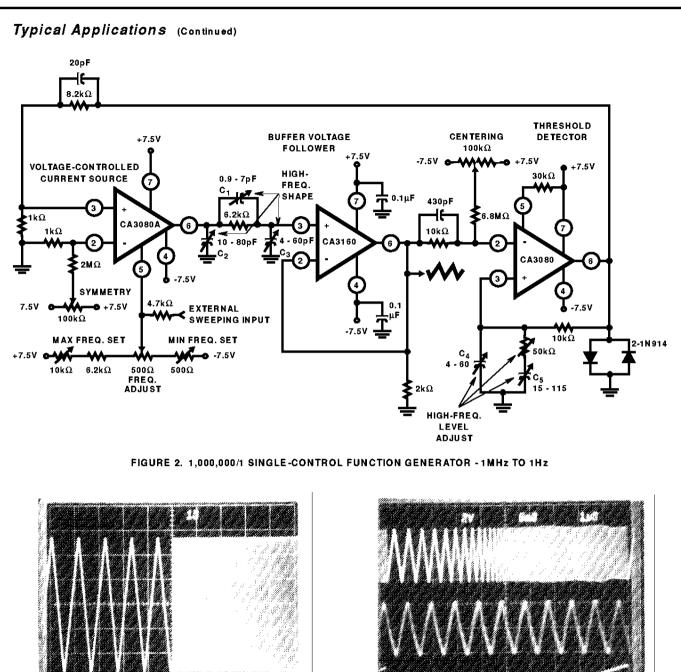


FIGURE 1. SCHEMATIC DIAGRAM OF THE CA3080 AND CA3080A IN A UNITY-GAIN VOLTAGE FOLLOWER CONFIGURATION AND ASSOCIATED WAVEFORM



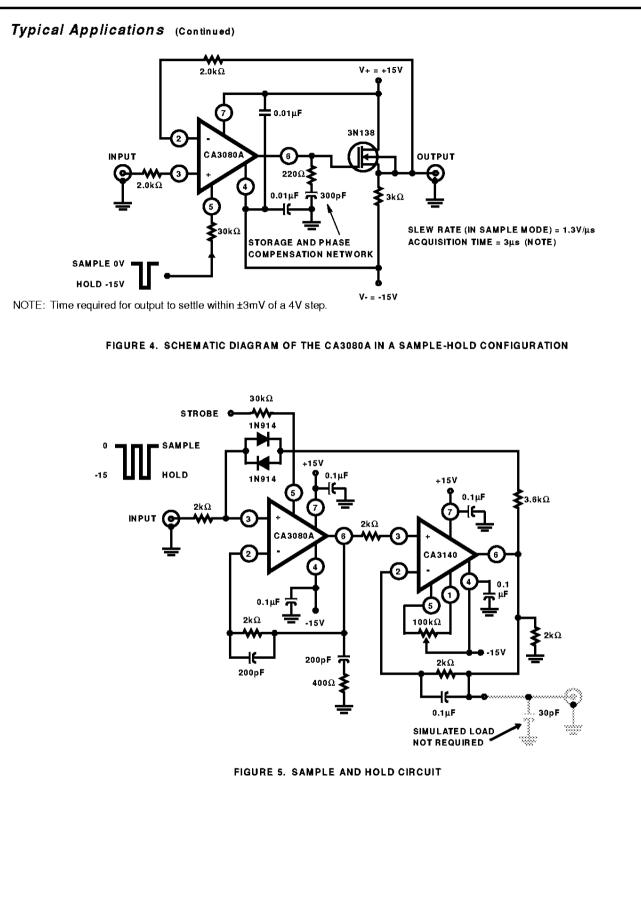
NOTE: A Square-Wave Signal Modulates The External Sweeping Input to Produce 1Hz and 1MHz, showing the 1,000,000/1 frequency range of the function generator.

FIGURE 3A. TWO-TONE OUTPUT SIGNAL FROM THE FUNCTION GENERATOR

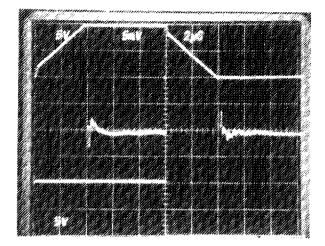
NOTE: The bottom trace is the sweeping signal and the top trace is the actual generator output. The center trace displays the 1MHz signal via delayed oscilloscope triggering of the upper swept output signal.

FIGURE 3B. TRIPLE-TRACE OF THE FUNCTION GENERATOR SWEEPING TO 1MHz

FIGURE 3. FUNCTION GENERATOR DYNAMIC CHARACTERISTICS WAVEFORMS

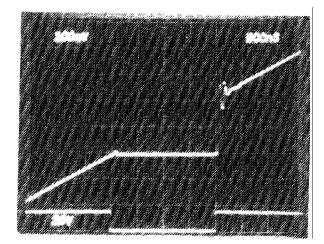


Typical Applications (Continued)



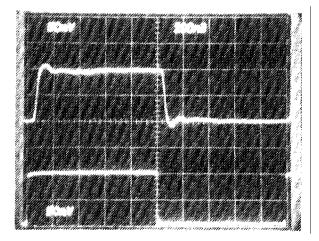
Top Trace:	Output Signal 5V/Div., 2µs/Div.
Bottom Trace:	Input Signal 5V/Div., 2μs/Div.
Center Trace:	Difference of Input and Output Signals Through Tektronix Amplifier 7A13 5mV/Div., 2μs/Div.

FIGURE 6. LARGE SIGNAL RESPONSE AND SETTLING TIME FOR CIRCUIT SHOWN IN FIGURE 23



Top Trace:System Output; 100mV/Div., 500ns/Div.Bottom Trace:Sampling Signal; 20V/Div., 500ns/Div.





Top Trace: Output; 50mV/Div., 200ns/Div. Bottom Trace: Input; 50mV/Div., 200ns/Div.

FIGURE 8. INPUT AND OUTPUT RESPONSE FOR CIRCUIT SHOWN IN FIGURE 23

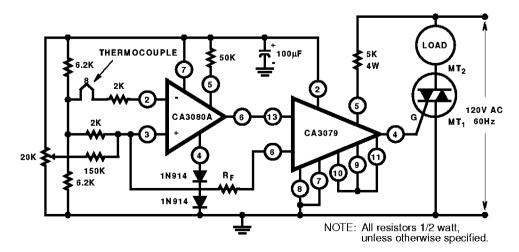
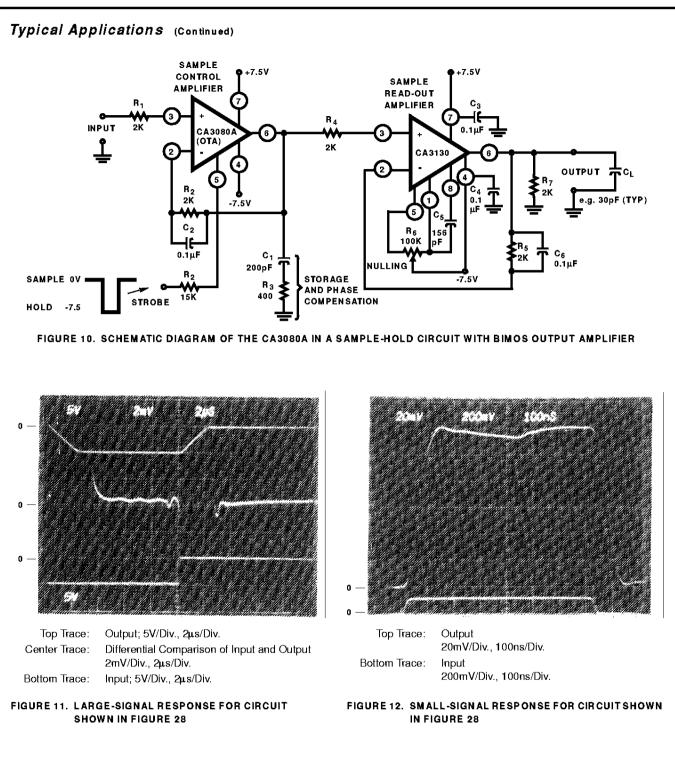
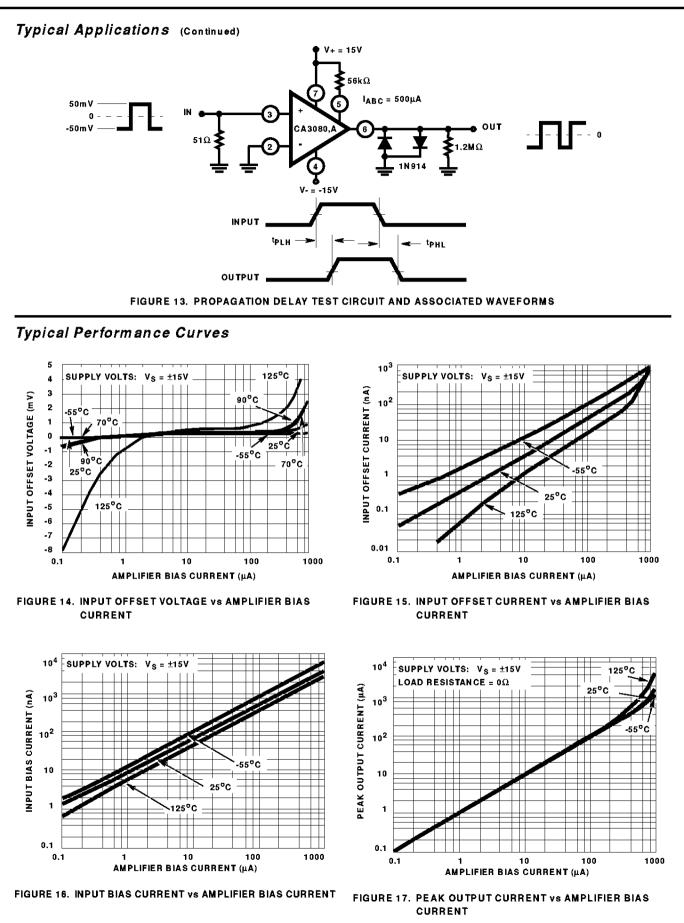
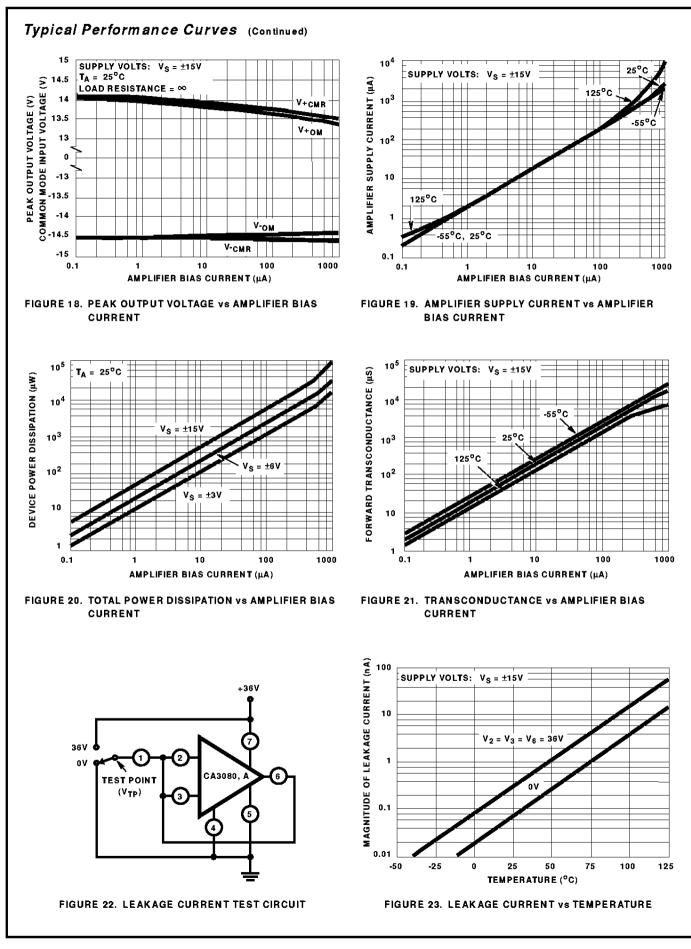


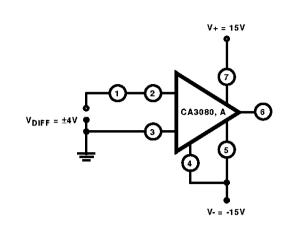
FIGURE 9. THERMOCOUPLE TEMPERATURE CONTROL WITH CA3079 ZERO VOLTAGE SWITCH AS THE OUTPUT AMPLIFIER







Typical Performance Curves (Continued)





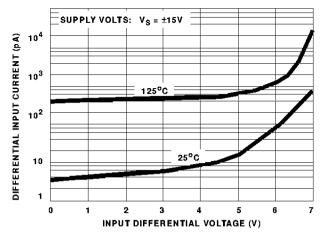


FIGURE 25. INPUT CURRENT vs INPUT DIFFERENTIAL VOLTAGE

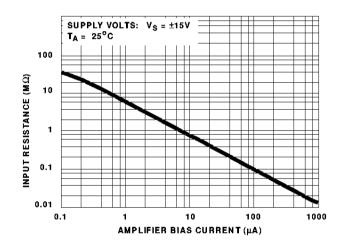


FIGURE 26. INPUT RESISTANCE VS AMPLIFIER BIAS CURRENT

7

6

5

4

3

2

1

۵ 0.1

(PF)

INPUT AND OUTPUT CAPACITANCE

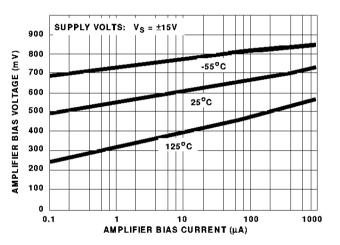
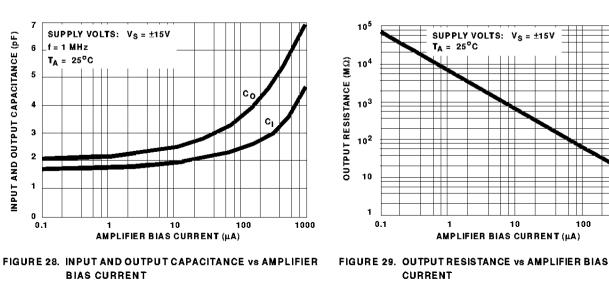


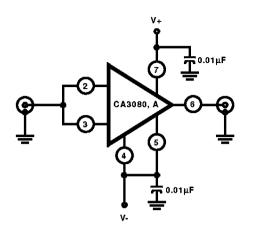
FIGURE 27. AMPLIFIER BIAS VOLTAGE vs AMPLIFIER BIAS CURRENT

100

1000



Typical Performance Curves (Continued)



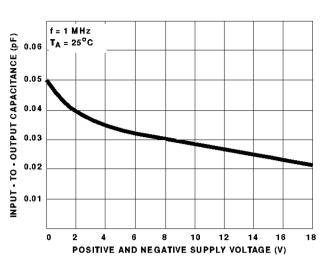


FIGURE 30. INPUT-TO-OUTPUT CAPACITANCE TEST CIRCUIT

FIGURE 31. INPUT-TO-OUTPUT CAPACITANCE VS SUPPLY VOLTAGE

All Harris Semiconductor products are manufactured, assembled and tested under ISO9000 quality systems certification.

Harris Semiconductor products are sold by description only. Harris Semiconductor reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Harris is believed to be accurate and reliable. However, no responsibility is assumed by Harris or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Harris or its subsidiaries.

Sales Office Headquarters

For general information regarding Harris Semiconductor and its products, call 1-800-4-HARRIS

NORTH AMERICA

Harris Semiconductor P. O. Box 883, Mail Stop 53-210 Melbourne, FL 32902 TEL: 1-800-442-7747 (407) 729-4984 FAX: (407) 729-5321

EUROPE

Harris Semiconductor Mercure Center 100, Rue de la Fusee 1130 Brussels, Belgium TEL: (32) 2.724.2111 FAX: (32) 2.724.22.05



ASIA Harris Semiconductor PTE Ltd. No. 1 Tannery Road Cencon 1, #09-01 Singapore 1334 TEL: (65) 748-4200 FAX: (65) 748-0400